



# PSMN2R0-60ES

N-channel 60 V 2.2 m $\Omega$  standard level MOSFET in I2PAK

Rev. 02 — 19 April 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	60	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	<a href="#">[1]</a> -	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	338	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 12</a>	<a href="#">[2]</a> -	1.8	2.2	m $\Omega$
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 100\text{ °C};$ see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	3	3.5	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 75\text{ A};$ $V_{DS} = 30\text{ V};$ see <a href="#">Figure 14</a> ;	-	32	-	nC
$Q_{G(tot)}$	total gate charge	see <a href="#">Figure 15</a>	-	137	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ $I_D = 120\text{ A}; V_{sup} \leq 60\text{ V};$ $R_{GS} = 50\text{ }\Omega;$ Unclamped	-	-	913	mJ

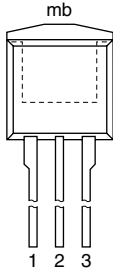
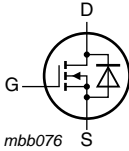


[1] Continuous current limited by package.

[2] Measured 3 mm from package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT226 (I2PAK)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
PSMN2R0-60ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

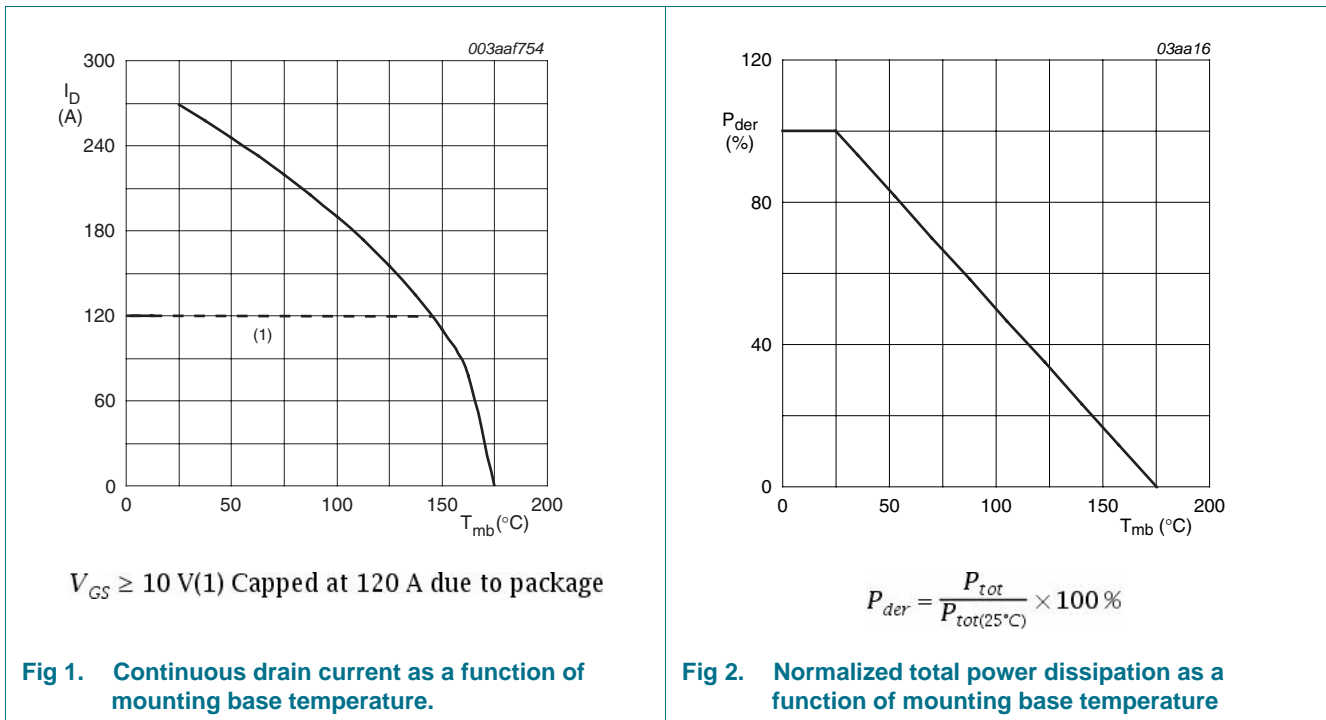
### 4. Limiting values

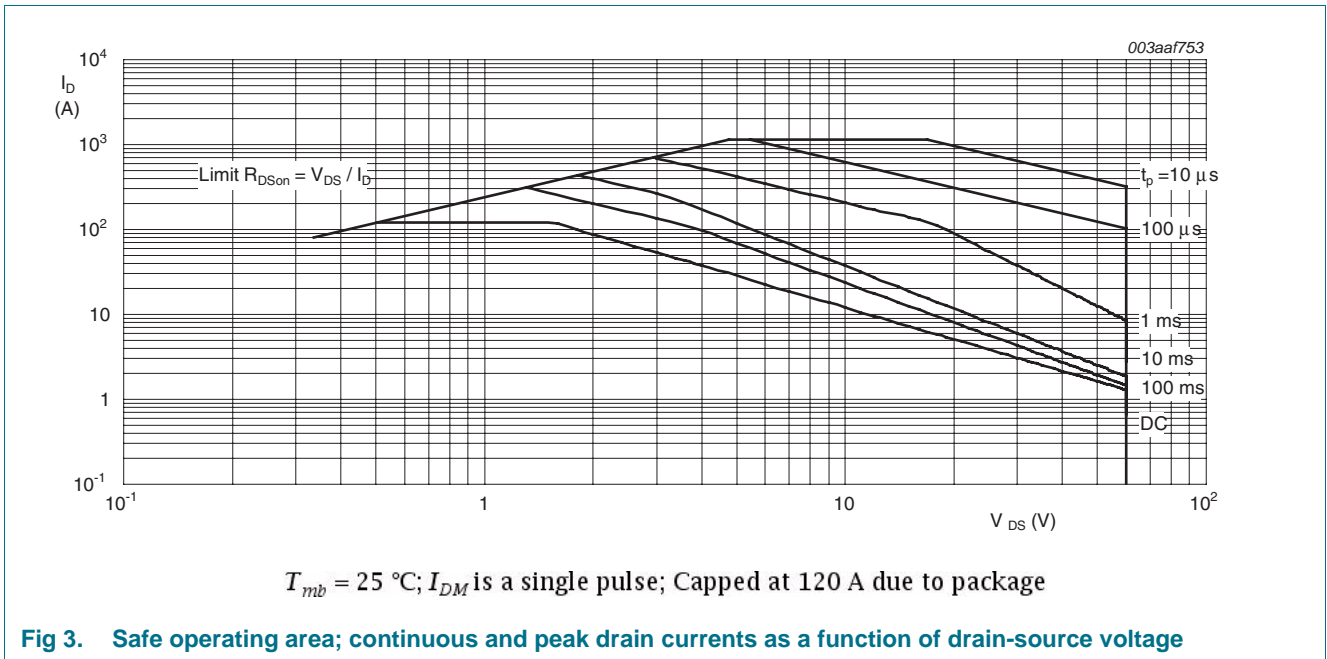
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	60	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a>	[1]	120	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a>	[1]	120	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	1135	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	338	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>slid(M)</sub>	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	1135	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 60 V; R <sub>GS</sub> = 50 Ω; Unclamped	-	913	mJ

[1] Continuous current limited by package





### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

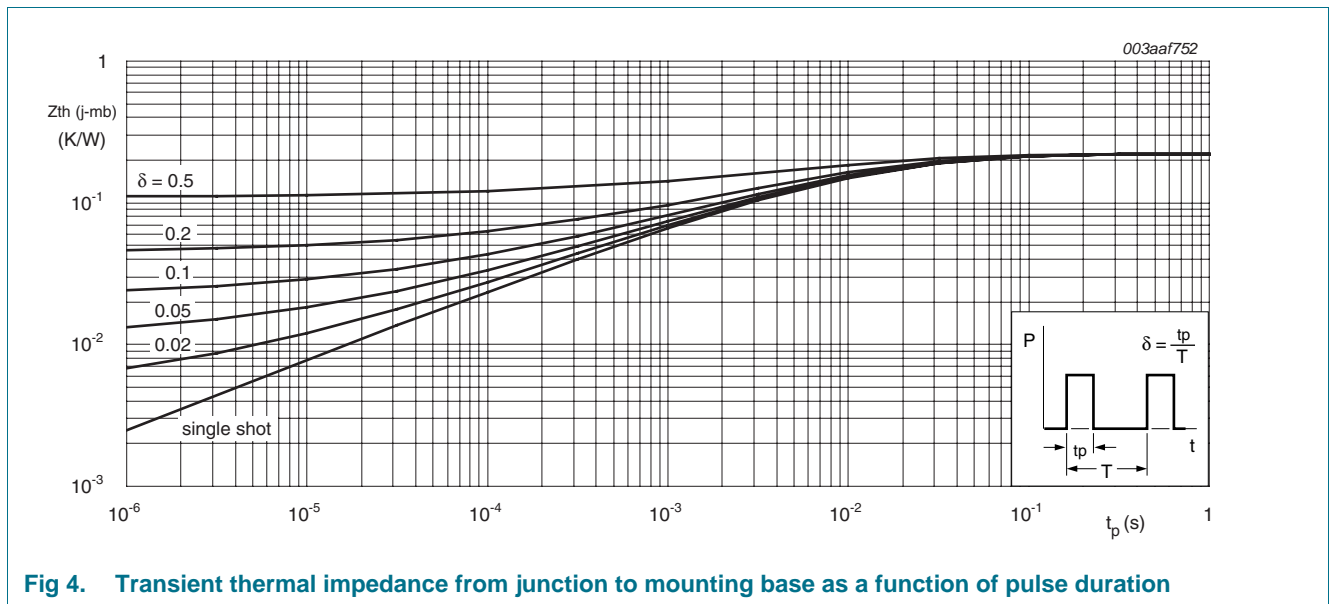


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

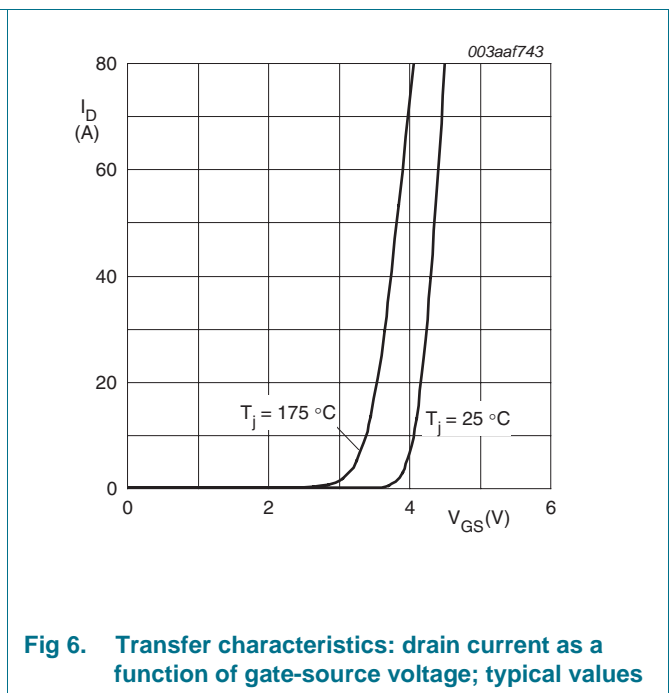
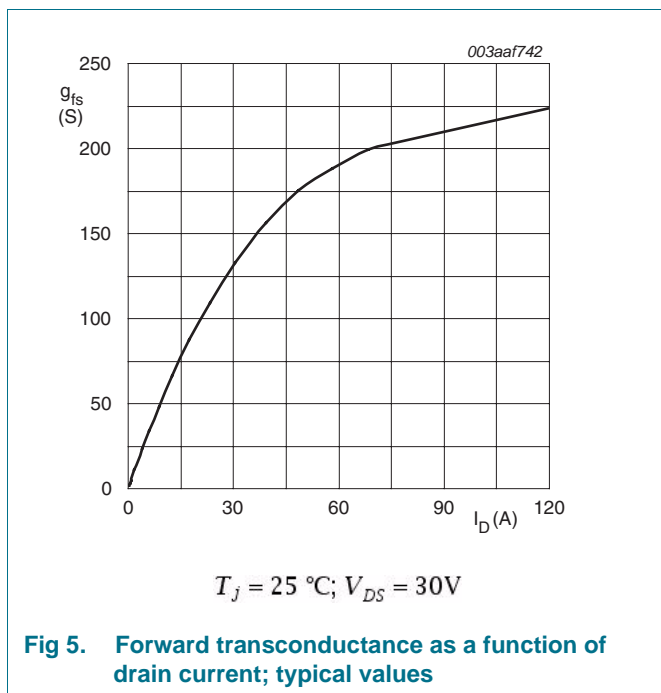
Table 6. Characteristics

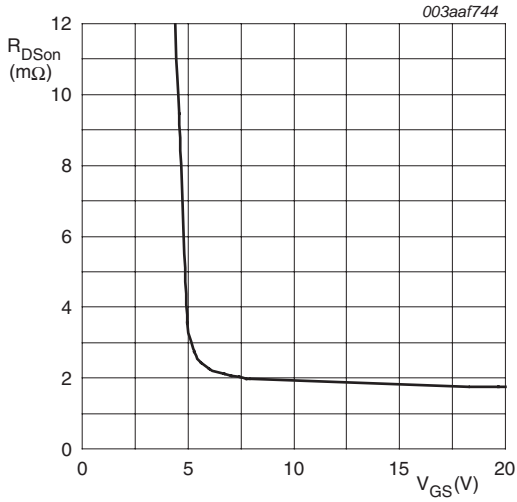
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	54	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 10</a>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 10</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 11</a> ; see <a href="#">Figure 10</a>	2	3	4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.03	10	$\mu A$
		$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 12</a>	<sup>[1]</sup> -	1.8	2.2	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	4.3	5.1	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 100 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	3	3.5	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	0.9	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	137	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	129	-	nC
$Q_{GS}$	gate-source charge	$I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V$	-	48	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	29	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	19	-	nC
$Q_{GD}$	gate-drain charge		-	32	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	5.7	-	V
$C_{iss}$	input capacitance	$V_{DS} = 30 V; V_{GS} = 0 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 16</a>	-	9997	-	pF
$C_{oss}$	output capacitance		-	1210	-	pF
$C_{rss}$	reverse transfer capacitance		-	594	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 V; R_L = 0.4 \text{ } \Omega; V_{GS} = 10 V; R_{G(ext)} = 4.7 \text{ } \Omega; I_D = 75 A$	-	42	-	ns
$t_r$	rise time		-	56	-	ns
$t_{d(off)}$	turn-off delay time		-	115	-	ns
$t_f$	fall time		-	49	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 30\text{ V}$	-	57	-	ns
$Q_r$	recovered charge	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 30\text{ V}$	-	80	-	nC

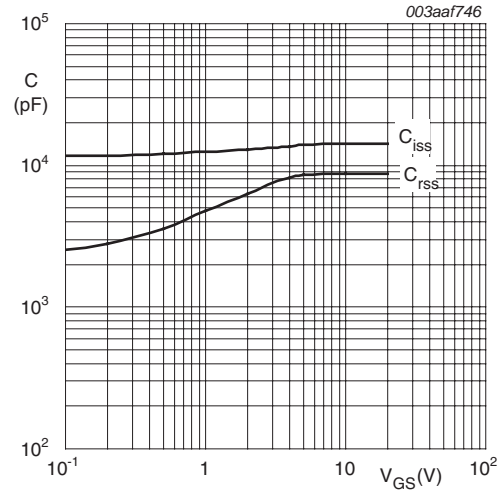
[1] Measured 3 mm from package.





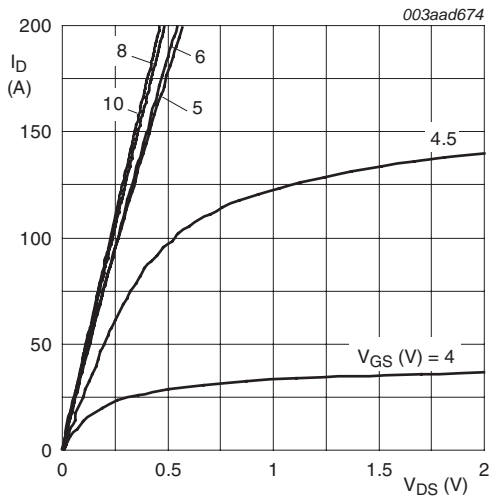
$T_j = 25\text{ °C}; I_D = 25\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



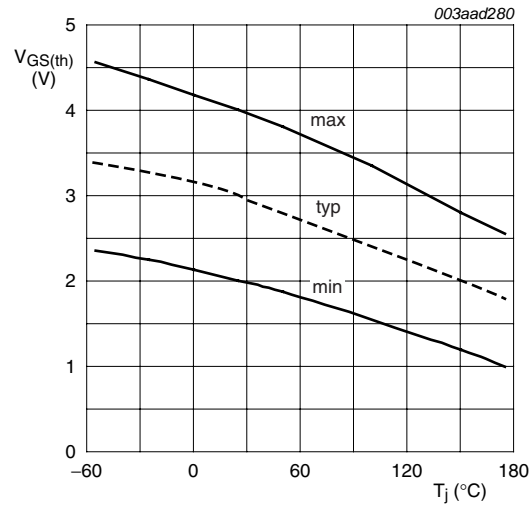
$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values



$T_j = 25\text{ °C}; t_p = 300\text{ }\mu\text{s}$

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



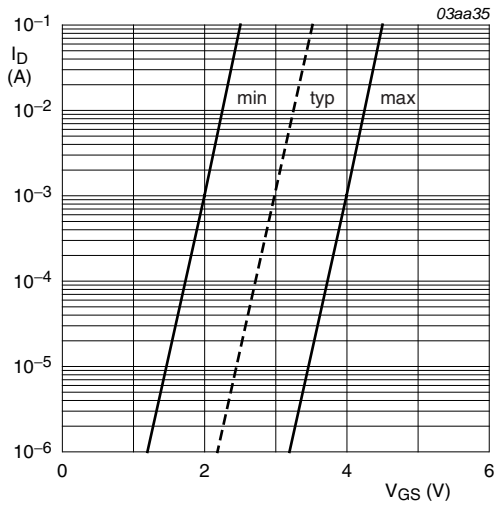


Fig 11. Sub-threshold drain current as a function of gate-source voltage

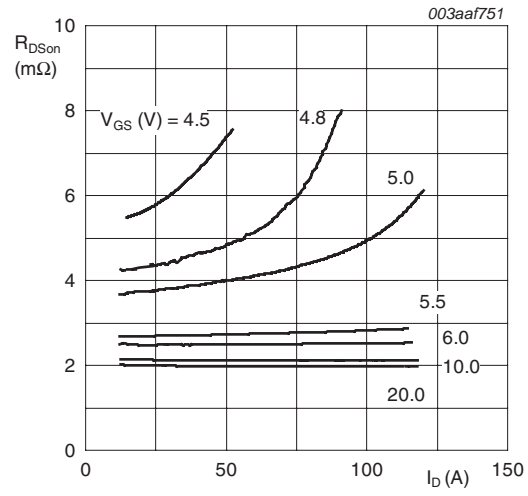


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

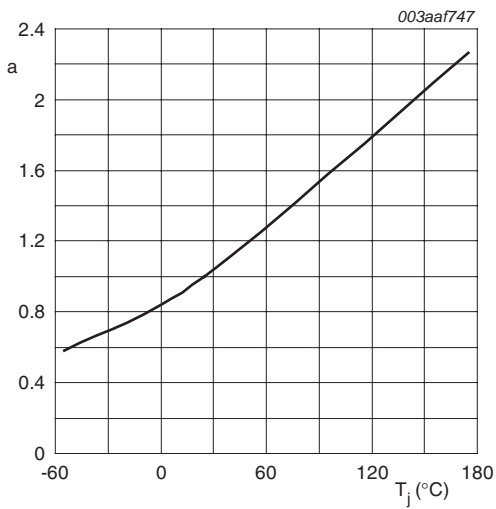


Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

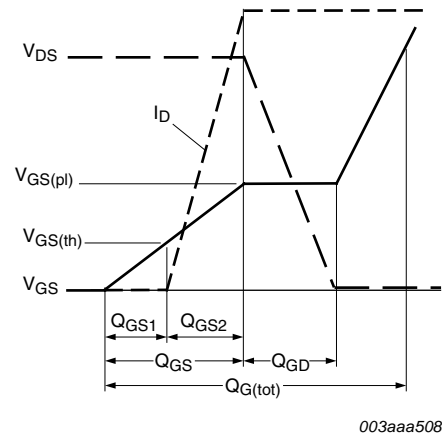
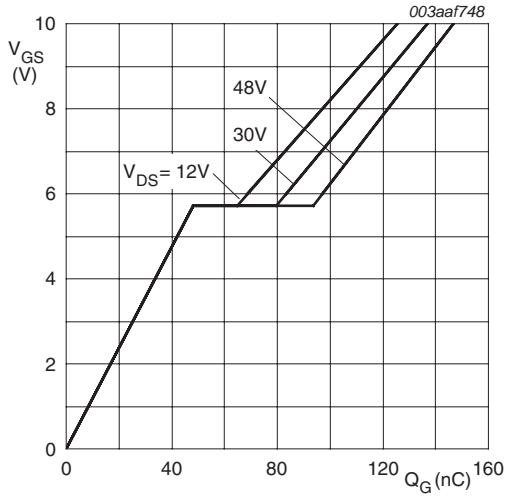
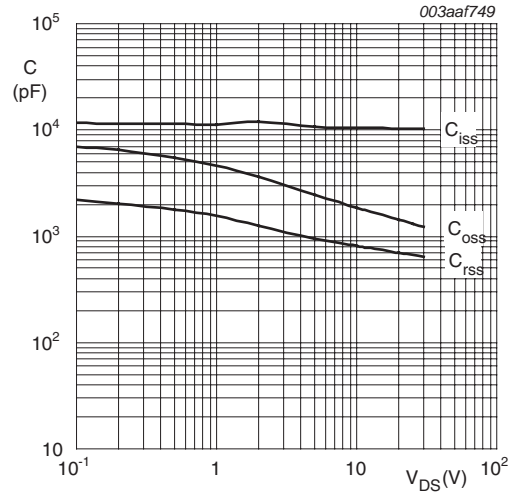


Fig 14. Gate charge waveform definitions



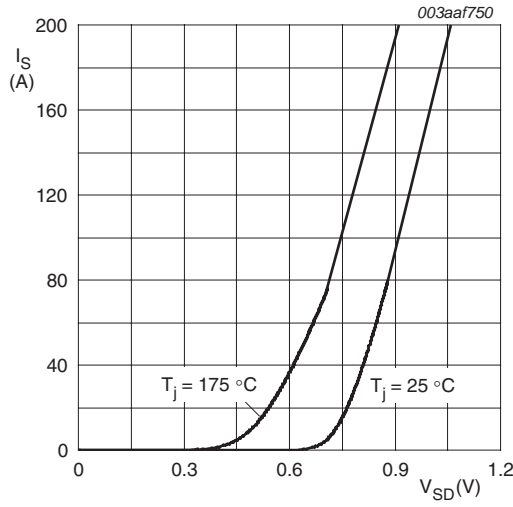
$T_j = 25\text{ }^\circ\text{C}; I_D = 75\text{ A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226

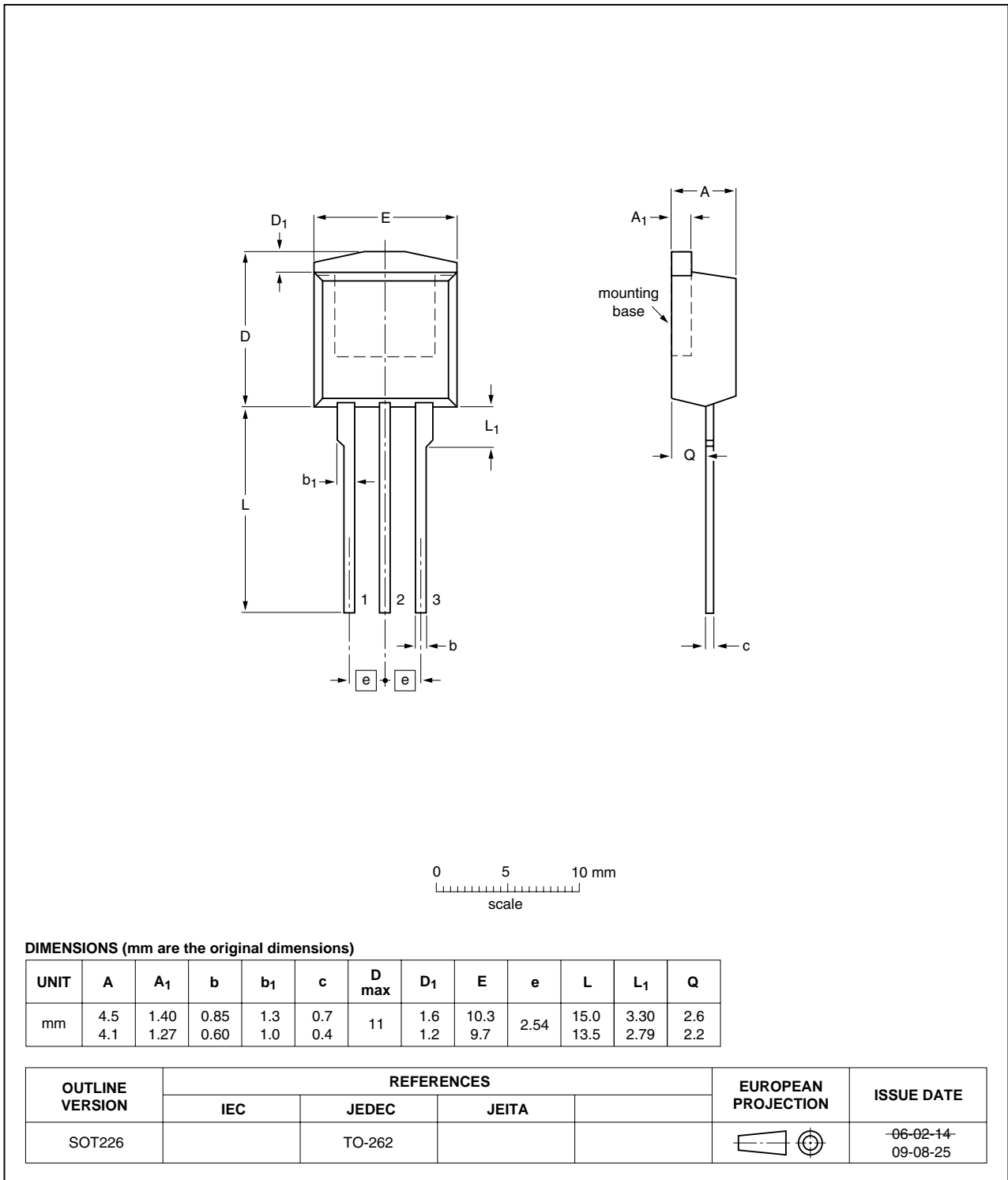


Fig 18. Package outline SOT226 (I2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R0-60ES v.2	20110419	Product data sheet	-	PSMN2R0-60ES v.1
Modifications:	<ul style="list-style-type: none"><li>• Status changed from objective to product.</li><li>• Various changes to content.</li></ul>			
PSMN2R0-60ES v.1	20110117	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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 Document identifier: PSMN2R0-60ES